

## ABSTRACT

A nonvolatile memory device capable of minimizing monitoring overhead associated with read disturb is provided. The nonvolatile memory device includes a memory cell array which includes a first cell string comprising a plurality of memory cells connected in series, wherein the plurality of memory cells includes a first monitoring cell, a first memory cell, and a second memory cell, and a row decoder which provides a first read voltage to the first memory cell and a first monitoring voltage to the first monitoring cell when reading the first memory cell among the memory cells and provides the first read voltage to the second memory cell and a second monitoring voltage different from the first monitoring voltage to the first monitoring cell when reading the second memory cell.

FIG. 1